

March 2008

# FDFMA2P029Z

# Integrated P-Channel PowerTrench® MOSFET and Schottky Diode

-20V, -3.1A, 95mΩ

### **Features**

### **MOSFET**

- Max  $r_{DS(on)}$  = 95m $\Omega$  at  $V_{GS}$  = -4.5V,  $I_D$  = -3.1A
- Max  $r_{DS(on)} = 141 \text{m}\Omega$  at  $V_{GS} = -2.5 \text{V}$ ,  $I_D = -2.5 \text{A}$
- HBM ESD protection level > 2.5kV (Note 3)

### Schottky

- V<sub>F</sub> < 0.37V @ 500mA
- Low profile 0.8 mm maximum in the new package MicroFET 2x2 mm
- RoHS Compliant



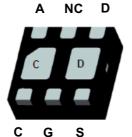
# **General Description**

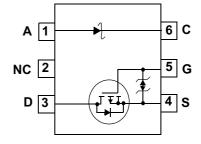
This device is designed specifically as a single package solution for the battery charge switch in cellular handset and other ultraportable applications. It features a MOSFET with very low onstate resistance and an independently connected low forward voltage schottky diode allows for minimum conduction losses.

The MicroFET 2X2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.

#### Pin 1







MicroFET 2X2 C G

## **MOSFET Maximum Ratings** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DS</sub>	Drain to Source Voltage		-20	V
$V_{GS}$	Gate to Source Voltage		±12	V
1	Drain Current -Continuous (No	te 1a)	-3.1	^
ID	-Pulsed		-6	A
D	Power Dissipation (No	te 1a)	1.4	W
$P_{D}$	(No	te 1b)	0.7	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C
$V_{RRM}$	Schottky Repetitive Peak Reverse Voltage		20	V
Io	Schottky Average Forward Current		2	Α

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	86	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	173	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1c)	86	C/VV
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1d)	140	

### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.P29	FDFMA2P029Z	MicroFET 2X2	7"	8mm	3000 units

# **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, referenced to 25°C		-12		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16V, \ V_{GS} = 0V$			-1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 12V, V_{DS} = 0V$			±10	μА

## On Characteristics

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-0.6	-1.0	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, referenced to 25°C		4		mV/°C
		$V_{GS} = -4.5V, I_{D} = -3.1A$		60	95	
r <sub>DS(on)</sub>	r <sub>DS(on)</sub> Static Drain to Source On-Resistance	$V_{GS} = -2.5V$ , $I_{D} = -2.5A$		88	141	mΩ
		$V_{GS} = -4.5V$ , $I_D = -3.1A$ , $T_J = 125$ °C		87	140	
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = -10V, I_{D} = -3.1A$		-11		S

# **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1MHz	ļ ļ	540	720	pF
C <sub>oss</sub>	Output Capacitance			120	160	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 1141112		100	150	pF

# **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		13	24	ns
t <sub>r</sub>	Rise Time	$V_{DD} = -10V, I_{D} = -1A$ $V_{GS} = -4.5V, R_{GEN} = 6\Omega$	11	20	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = -4.5V, N <sub>GEN</sub> = 012	37	59	ns
t <sub>f</sub>	Fall Time		36	58	ns
Q <sub>g(TOT)</sub>	Total Gate Charge	$V_{DD} = -10V, I_{D} = -3.1A$	7	10	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	V <sub>GS</sub> = -4.5V	1.1		nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge		2.4		nC

# **Drain-Source Diode Characteristics**

Is	Maximum Continuous Drain-Source Diode Forward Current			-1.1	Α
V <sub>SD</sub>	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_S = -1.1A$ (Note 2)	-0.8	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>E</sub> = -3.1A, di/dt = 100A/μs	25		ns
Q <sub>rr</sub>	Reverse Recovery Charge	ης – –3. 1Α, αναί – 100Α/μδ	9		nC

## **Schottky Diode Characteristics**

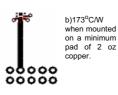
$V_R$	Reverse Voltage	I <sub>R</sub> = 1mA	T <sub>J</sub> = 25°C	20			V
	Poverse Leekege	V = 20V	T <sub>J</sub> = 25°C		30	300	μΑ
<sup>I</sup> R	Reverse Leakage	V <sub>R</sub> = 20V	$T_{J} = 125^{\circ}C$		10	45	mA
		I <sub>F</sub> = 500mA	T <sub>J</sub> = 25°C		0.32	0.37	
V		IF - 200111A	$T_{J} = 125^{\circ}C$		0.21	0.26	V
V <sub>F</sub> Forward Voltage	Forward voitage	1 – 40	T <sub>J</sub> = 25°C		0.37	0.435	V
		I <sub>F</sub> = 1A	$T_{J} = 125^{\circ}C$		0.28	0.33	

#### Notes:

- 1: R<sub>BJA</sub> is determined with the device mounted on a 1 in<sup>2</sup> oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>BJC</sub> is guaranteed by design while R<sub>BJA</sub> is determined by the user's board design.
  - (a) MOSFET  $R_{\theta JA}$  = 86°C/W when mounted on a 1in<sup>2</sup> pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB
  - (b) MOSFET  $R_{\theta JA}$  = 173°C/W when mounted on a minimum pad of 2 oz copper
  - (c) Schottky R $_{\theta JA}$  = 86°C/W when mounted on a 1in $^2$  pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB.
  - (d) Schottky  $R_{\theta JA}$  = 140°C/W when mounted on a minimum pad of 2 oz copper.



a)86°C/W when mounted on a 1in² pad of 2 oz copper.





c)86°C/W when mounted on a 1in² pad of 2 oz copper.



d)140°C/W when mounted on a minimum pad of 2 oz copper.

- 2: Pulse Test: Pulse Width < 300us, Duty Cycle < 2.0%
- 3. The diode connected between the gate and source serves only protection against ESD. No gate overvoltage rating is implied.



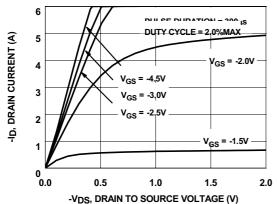


Figure 1. On Region Characteristics

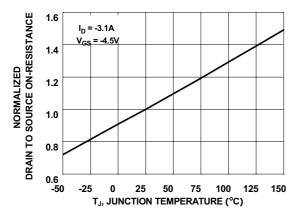


Figure 3. Normalized On-Resistance vs Junction Temperature

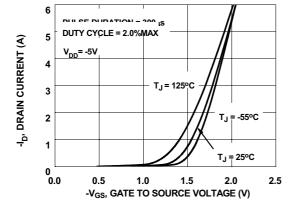


Figure 5. Transfer Characteristics

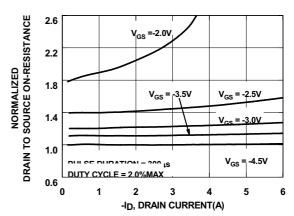


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

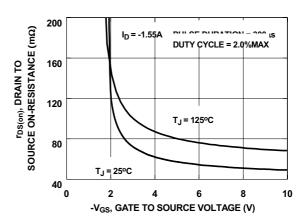


Figure 4. On-Resistance vs Gate to Source Voltage

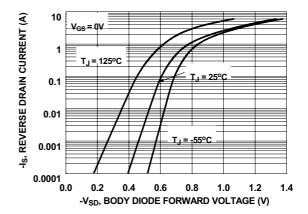


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# **Typical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

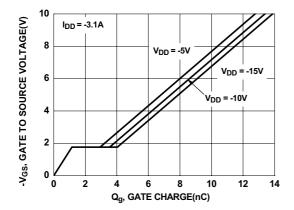


Figure 7. Gate Charge Characteristics

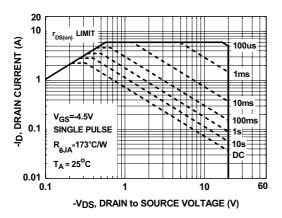


Figure 9. Forward Bias Safe Operating Area

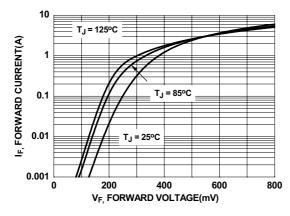


Figure 11. Schottky Diode Forward Voltage

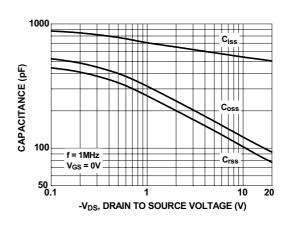


Figure 8. Capacitance Characteristics

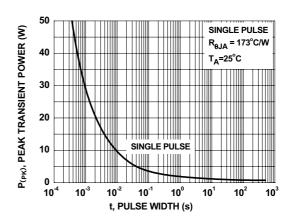


Figure 10. Single Pulse Maximum Power Dissipation

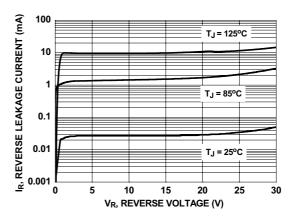


Figure 12. Schottky Diode Reverse Current

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

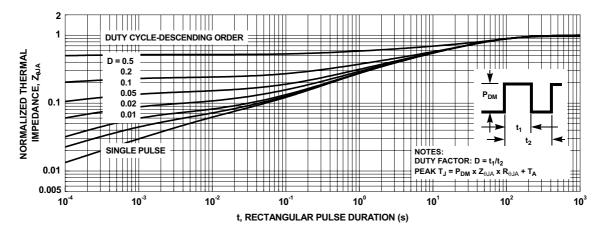
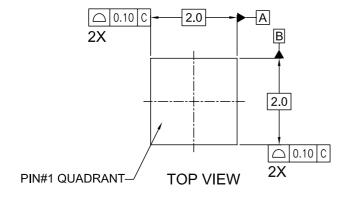
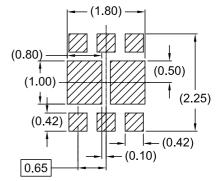


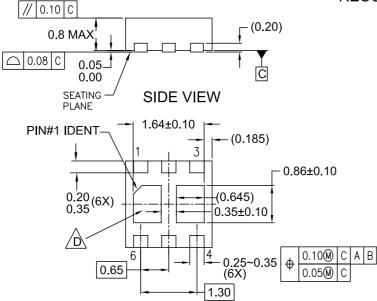
Figure 13. Transient Thermal Response Curve

# **Dimensional Outline and Pad Layout**





RECOMMENDED LAND PATTERN



**BOTTOM VIEW** 

# NOTES:

- A. CONFORMS TO JEDEC REGISTRATION MO-229, VARIATION VCCC EXCEPT AS NOTED.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
- NON-JEDEC DUAL DAP
- E. DRAWING FILE NAME : MLP06Jrev3





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